José Menéndez

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PERSONAL

Born in Tandil, Argentina, in 1957. US Citizen.

EMPLOYMENT

Professor of Physics 1998-Present
ARIZONA STATE UNIVERSITY TEMPE, AZ

Associate Professor of Physics 1992-1998
ARIZONA STATE UNIVERSITY TEMPE, AZ

Contractor1997MOTOROLA, INCMESA, AZ

Assistant Professor of Physics 1987-1992
ARIZONA STATE UNIVERSITY TEMPE, AZ

Consultant1988-1989AT&T BELL LABORATORIESTEMPE, AZ

Postdoctoral Member of Technical Staff
AT&T Bell Laboratories

1985-1987
MURRAY HILL, NJ

Research AssociateMAX-PLANCK-INSTITUT FÜR FESTKÖRPERFORSCHUNG
STUTTGART, GERMANY

EDUCATION

Dr. rer. nat. 1985

UNIVERSITÄT STUTTGART STUTTGART, GERMANY

Major: Physics

Thesis: Ramanspektroscopische Untersuchungen der Phonon-Phonon und Elektron-Phonon

Wechselwirkungen in tetraedisch koordinierten Halbleitern (Raman Investigations of the

phonon-phonon and electron-phonon interactions in tetrahedral semiconductors).

Advisor: Prof. Dr. Dr. h.c. Manuel Cardona i Castro.

Licenciado 1980

Instituto Balseiro Bariloche, Argentina

Major: Physics

Thesis: Espectroscopía de electrones en cerio metálico (Electron Spectroscopy in metallic

Cerium)

Advisor: Prof. Dr. Raúl Baragiola

MEMBERSHIPS

American Physical Society. Materials Research Society. Elected Member-at-Large for the Forum on International Physics (APS) for 1999-2001.

HONORS

1990	Presidential Young Investigator Award
1998	Iberdrola Fellow (Universidad Autónoma de Madrid, Madrid, Spain)
2002	Dean's Quality of Teaching Award, College of Liberal Arts and Sciences, ASU.
2003	Focus Center Fellow, University of Michigan, Ann Arbor.
2008	American Physical Society Outstanding Referee.
2009	Outstanding Teaching Award, Department of Physics, ASU.

REFEREED JOURNAL PUBLICATIONS

- 1. V. R. D'Costa, Y. Fang, J. Mathews, R. Roucka, J. Tolle, J. Menendez, and J. Kouvetakis, "Snalloying as a means of increasing the optical absorption of Ge at the *C* and *L*-telecommunication bands," Semicond. Sci. Technol. **24**, 115006 (2009).
- 2. J. Mathews, R. Roucka, J. Q. Xie, S. Q. Yu, J. Menéndez, and J. Kouvetakis, "Extended performance GeSn/Si(100) p-i-n photodetectors for full spectral range telecommunication applications," Appl. Phys. Lett. **95** 133506 (2009).
- 3. V. R. D'Costa, J. Tolle, J. Q. Xie, J. Kouvetakis, and J. Menéndez, "Infrared dielectric function of p-type Ge_{0.98}Sn_{0.02} alloys," Phys. Rev. B **80** 125209 (2009).
- 4. J. Q. Xie, J. Tolle, V. R. D'Costa, C. Weng, A. V. G. Chizmeshya, J. Menéndez, and J. Kouvetakis, "Molecular approaches to *p* and *n*-nanoscale doping of Ge_{1-y}Sn_y semiconductors: Structural, electrical and transport properties," Solid-State Electronics **53**, 816 (2009).
- 5. J. Tolle, R. Roucka, B. Forrest, A. V. G. Chizmeshya, J. Kouvetakis, V. R. D'Costa, C. D. Poweleit, M. Groenert, T. Sato, and J. Menéndez, "Integration of Zn-Cd-Te-Se Semiconductors on Si Platforms via Structurally Designed Cubic Templates Based on Group IV Elements," Chemistry Of Materials **21**, 3143 (2009).
- J. B. Tice, C. G. Weng, J. Tolle, V. R. D'Costa, R. Singh, J. Menéndez, J. Kouvetakis, and A. V.
 G. Chizmeshya, "Ether-like Si-Ge hydrides for applications in synthesis of nanostructured semiconductors and dielectrics," Dalton Transactions 34 6773 (2009).
- 7. Y. Y. Fang, J. Tolle, A. V. G. Chizmeshya, J. Kouvetakis, V. R. D'Costa, and J. Menéndez, "Practical B and P doping via Si_xSn_yGe_{1-x-y-z}M_z quaternaries lattice matched to Ge: Structural, electrical, and strain behavior," Appl. Phys. Lett. **95** 081113 (2009).
- 8. José Menéndez, "Analytical strain relaxation Model for $Si_{1-x}Ge_x$ epitaxial layers," J. Appl. Phys. **105**, 063519 (2009).
- 9. V. R. D'Costa, Y. Y. Fang, J. Kouvetakis, and J. Menéndez, "Tunable Optical Gap at a Fixed Lattice Constant in Group-IV Semiconductor Alloys," Phys. Rev. Lett. **102**, 107403 (2009).
- 10. Y. Y. Fang, V. R. D'Costa, J. Tolle, J. B. Tice, C. D. Poweleit, J. Menéndez, and J. Kouvetakis,

- "Highly strained metastable structures and selective area epitaxy of Ge-rich $Ge_{1-x}Si_x$ /Si(100) materials using nanoscale building blocks," Solid State Commun. **149**, 78 (2009).
- 11. R. Roucka, Y. J. An, A. V. G. Chizmeshya, V. R. D'Costa, J. Tolle, J. Menéndez, and J. Kouvetakis, "Structural and optical properties of ZrB₂ and Hf_x Zr_{1-x}B₂ films grown by vicinal surface epitaxy on Si(111) substrates," Solid State Electr. **52**, 1687 (2008).
- Y. Y. Fang, J. Xie, J. Tolle, R. Roucka, V. R. D'Costa, A.V.G. Chizmeshya, J. Menéndez, and J. Kouvetakis, "A molecular-based synthetic approach to new group-IV materials for high efficiency, low cost solar cells and Si-based optoelectronics," J. Am. Chem. Soc. 130, 16095 (2008).
- 13. R. Roucka, J. Xie, J. Kouvetakis, J. Mathews, V. D. Costa, J. Menéndez, J. Tolle, and S. Q. Yu, "Ge_{1-y}Sn_y photoconductor structures at 1.55 microns: From advanced materials to prototype devices," J. Vac. Sci. Technol. B **26**, 1952 (2008).
- 14. Y. Y. Fang, V. R. D'Costa, J. Tolle, C. D. Poweleit, J. Kouvetakis, and J. Menéndez, Strained Si films grown by chemical vapor deposition of trisilane on Ge buffered Si(100)," Thin Solid Films **516**, 8327 (2008).
- 15. N. Bonini, R. Rao, A. M. Rao, N. Marzari, and J. Menéndez, "Lattice anharmonicity in low-dimensional carbon systems" Phys. Stat. Sol. (b) **245**, 2149 (2008).
- 16. J. Kouvetakis, Y. J. An, V. R. D'Costa, J. Tolle, A. V. G. Chizmeshya, and J. Menéndez, "Synthesis of (Hf, Zr)B₂-based heterostructures: hybrid substrate systems for low temperature Al-Ga-N integration with Si," J. Mater. Chem. **18**, 4775 (2008).
- 17. R. Roucka, V. R. D'Costa, Y. J. An, M. Canonico, J. Kouvetakis, J. Menéndez, and A. V. G. Chizmeshya, "Thermoelastic and optical properties of thick boride templates on silicon for nitride integration applications," Chem. Mater. **20**, 1431 (2008).
- Yan-Yan Fang, J. Tolle, J. Tice, A.V.G. Chizmeshya, J. Kouvetakis, V.R. D'Costa, and J. Menéndez, "Epitaxy driven synthesis of elemental Ge/Si materials and devices with strained engineered structures via designer molecular chemistry," Chemistry of Materials 19 (24), 5910-5925 (2007).
- R. Rao, J. Menendez, C. D. Poweleit, and A. M. Rao, "Anharmonic Phonon Lifetimes in Carbon Nanotubes: Evidence for a One-Dimensional Phonon Decay Bottleneck," Phys. Rev. Lett. 99, 047403 (2007).
- 20. G. Sun, H.H. Cheng, J. Menéndez, J.B Khurgin, R.A. Soref, "Strain-free Ge/GeSiSn quantum cascade lasers based on L-valley intersubband transitions," Appl. Phys. Lett. **90**, 251105 (2007).
- 21. V. R. D'Costa, J. Tolle, R. Roucka, C. D. Poweleit, J. Kouvetakis, and J. Menéndez, "Raman Scattering in Ge_{1-v} Sn_v alloys," Solid State Commun. **144** (5-6), 240 (2007).
- 22. V. R. D'Costa, J. Tolle, C. D. Poweleit, J. Kouvetakis, and J. Menendez, "Compositional dependence of Raman frequencies in ternary $Ge_{1-x-y}Si_xSn_y$ alloys," Phys. Rev. B **76**, 035211 (2007).
- 23. Y. Y. Fang, J. Tolle, R. Roucka, A. V. G. Chizmeshya, J. Kouvetakis, V. R. D'Costa, and J. Menendez, "Perfectly tetragonal, tensile-strained Ge on Ge_{1-x-y}Sn_y buffered Si(100)," Appl. Phys. Lett. **90**, 061915 (2007).
- 24. R. Roucka, J. Tolle, B. Forrest, J. Kouvetakis, V. R. D'Costa, and J. Menéndez, " $Ge_{1-y}Sn_y$ /Si(100) composite substrates for growth of In_x $Ga_{1-x}As$ and $GaAs_{1-x}Sb_x$ alloys," J. Appl. Phys. **101**, 013518 (2007).

- 25. J. Kouvetakis, J. Menéndez, and A.V.G Chizmeshya, "Tin-based group IV semiconductors: New Platforms for opto- and microelectronics on silicon," Ann. Rev. Mat. Res. **36**, 497-554 (2006).
- 26. R. Roucka, Y. An, A. V. G. Chizmeshya, J. Tolle, J. Kouvetakis, V. R. D'Costa, J. Menéndez, and P. Crozier, "Epitaxial semimetallic Hf_xZr_{1-x}B₂ templates for optoelectronic integration on silicon," Appl. Phys. Lett. **89**, 242110 (2006).
- 27. J. Tolle, A. V. G. Chizmeshya, Y. Y. Fang, J. Kouvetakis, V.R. D'Costa, C.W. Hu, J. Menéndez, I.S.T. Tsong, "Low temperature chemical vapor deposition of Si-based compounds via SiH₃SiH₂SiH₃: Metastable SiSn/GeSn/Si(100) heteroepitaxial structures," Appl. Phys. Lett. **89**, 231924 (2006).
- 28. V. G. Chizmeshya, C. Ritter, J. Tolle, C. Cook, J. Menendez, and J. Kouvetakis, "Fundamental Studies of P(GeH₃)₃, As(GeH₃)₃, and Sb(GeH₃)₃: Practical n-Dopants for New Group IV Semiconductors," Chem. Mater. **18**, 6266 (2006).
- 29. V.R. D'Costa, C.S. Cook, A.G. Birdwell C.L. Litter, M. Canonico, S. Zollner, J. Kouvetakis, and J. Menéndez, "Optical critical points of thin-film Ge_{1-y}Sn_y alloys: a comparative Ge_{1-y}Sn_y/Ge_{1-x}Si_x study,"Phys. Rev. B **73** 125207 (2006).
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- 31. J. Tolle, R.Roucka, A.V.G. Chizmeshya, J. Kouvetakis, V.R. D'Costa, and J. Menéndez, "Compliant tin-based buffers for the growth of defect-free strained heterostructures on silicon," Appl. Phys. Lett. **88** 252112 (2006).
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- 33. C.-W. Hu, J. Menéndez, I.S.T. Tsong, J. Tolle, A.V.G. Chizmeshya, C. Ritter, J. Kouvetakis "Low temperature pathways to Ge-rich Si_{1-x}Ge_x alloys via single-source hydride chemistry," Appl. Phys. Lett. **87** 181903 (2005).
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- 36. C. Aku-Leh, J. Zhao, R. Merlin, J. Menéndez, and M. Cardona, "Long-lived optical phonons in ZnO studied with impulsive stimulated Raman scattering," Phys. Rev. B **71** 205211 (2005).
- 37. R. Roucka, J. Tolle, C. Cook, A.V.G. Chizmeshya, J. Kouvetakis, V. D'Costa, J. Menéndez, Z.D. Chen, and S. Zollner, "Versatile buffer layer architectures based on Ge_{1-x}Sn_x alloys," Appl. Phys. Lett. **86**, 191912 (2005).
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- 40. C.S. Cook, S. Zollner, M.R. Bauer, P. Aella, J. Kouvetakis, and J. Menéndez, "Optical constants and interband transitions of $Ge_{1-x}Sn_x$ alloys (x < 0.2) grown on Si by UHV-CVD, " Thin Solid Films **455-456**, 217-21 (2004).
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- 45. M. Bauer, C. Ritter, P.A. Crozier, J. Ren, J. Menéndez, G. Wolf, and J. Kouvetakis, "Synthesis of ternary SiGeSn semiconductors on Si(100) via Sn_xGe_{1-x} buffer layers," Appl. Phys. Lett. **83**, 2163-5 (2003).
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- G.H. Loechelt, N.G. Cave, and J. Menéndez, "Polarized off-axis Raman spectroscopy: A technique for measuring stress tensors in semiconductors," J. of Applied Physics, 86, 6164-80 (1999).

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